2SB1462J

Silicon PNP epitaxial planar type

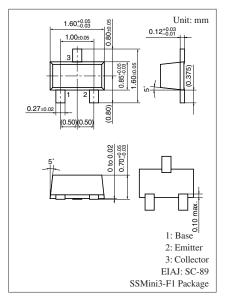
For general amplification Complementary to 2SD2216J

■ Features

- High forward current transfer ratio h_{FE}
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-60	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Emitter-base voltage (Collector open)	V_{EBO}	-7	V	
Collector current	I_C	-100	mA	
Peak collector current	I_{CP}	-200	mA	
Collector power dissipation	P _C	125	mW	
Junction temperature	T_{j}	125	°C	
Storage temperature	T_{stg}	-55 to +125	°C	

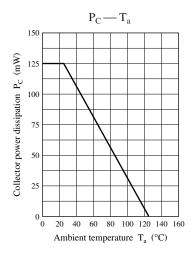


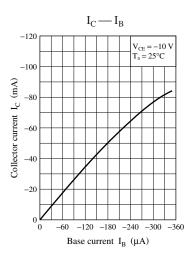
Marking Symbol: A

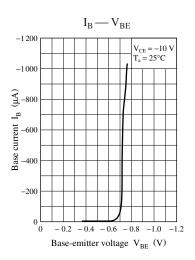
\blacksquare Electrical Characteristics $T_a = 25 ^{\circ}C \pm 3 ^{\circ}C$

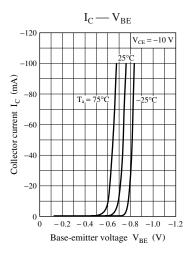
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \; \mu \text{A}, \; I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -100 \mu\text{A}, I_B = 0$	-50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu A, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}, I_{E} = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = -10 \text{ V}, I_{E} = 0$			-100	μΑ
Forward current transfer ratio	h_{FE}	$V_{CE} = -10 \text{ V}, I_{C} = -2 \text{ mA}$	180		390	_
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		- 0.3	- 0.5	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2.7		pF
(Common base, input open circuited)						

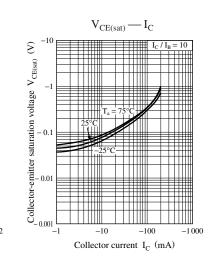
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

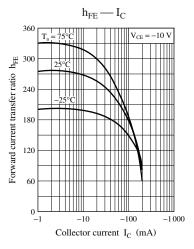


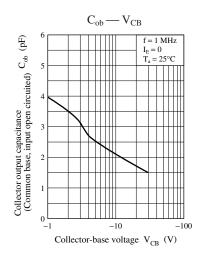












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